Preferred Device

Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supply crowbar circuits.

- Glass Passivated Junctions with Center Gate Fire for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Constructed for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 800 Volts
- 300 A Surge Current Capability
- Device Marking: Logo, Device Type, e.g., 2N6504, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
*Peak Repetitive Off–State Voltage (Note 1.) (Gate Open, Sine Wave 50 to 60 Hz, T _J = 25 to 125°C)	V _{DRM,} V _{RRM}		Volts
2N6504 2N6505 2N6507 2N6508 2N6509		50 100 400 600 800	
On-State RMS Current (180° Conduction Angles; T _C = 85°C)	I _{T(RMS)}	25	А
Average On-State Current (180° Conduction Angles; T _C = 85°C)	I _{T(AV)}	16	Α
Peak Non-repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T _J = 100°C)	I _{TSM}	250	Α
Forward Peak Gate Power (Pulse Width ≤ 1.0 μs, T _C = 85°C)	P _{GM}	20	Watts
Forward Average Gate Power (t = 8.3 ms, T _C = 85°C)	P _{G(AV)}	0.5	Watts
Forward Peak Gate Current (Pulse Width ≤ 1.0 μs, T _C = 85°C)	I _{GM}	2.0	А
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

*Indicates JEDEC Registered Data

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



ON Semiconductor™

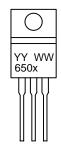
http://onsemi.com

SCRs 25 AMPERES RMS 50 thru 800 VOLTS



MARKING DIAGRAM





PIN ASSIGNMENT		
1	Cathode	
2	Anode	
3	Gate	
4	Anode	

WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
2N6504	TO220AB	500/Box
2N6505	TO220AB	500/Box
2N6507	TO220AB	500/Box
2N6508	TO220AB	500/Box
2N6509	TO220AB	500/Box

Preferred devices are recommended choices for future use and best overall value.

*THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

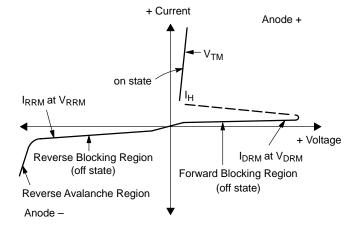
Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
*Peak Repetitive Forward or Reverse Blocking Current $(V_{AK} = Rated \ V_{DRM} \ or \ V_{RRM}, \ Gate \ Open)$	T _J = 25°C T _J = 125°C	I _{DRM} , I _{RRM}	_ _	_ _	10 2.0	μA mA
ON CHARACTERISTICS						
*Forward On–State Voltage (Note 2.) (I _{TM} = 50 A)		V_{TM}	_	_	1.8	Volts
*Gate Trigger Current (Continuous dc) (V _{AK} = 12 Vdc, R _L = 100 Ohms)	$T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	I _{GT}		9.0 -	30 75	mA
*Gate Trigger Voltage (Continuous dc) $(V_{AK} = 12 \text{ Vdc}, R_L = 100 \text{ Ohms}, T_C = -40^{\circ}\text{C})$		V _{GT}	_	1.0	1.5	Volts
Gate Non-Trigger Voltage (V _{AK} = 12 Vdc, R _L = 100 Ohms, T _J = 125°C)		$V_{\sf GD}$	0.2	_	_	Volts
*Holding Current (V _{AK} = 12 Vdc, Initiating Current = 200 mA, Gate Open)	$T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	Ін	-	18	40 80	mA
*Turn-On Time (I _{TM} = 25 A, I _{GT} = 50 mAdc)	10 - 40 0	t _{gt}		1.5	2.0	μs
Turn-Off Time (V_{DRM} = rated voltage) (I_{TM} = 25 A, I_{R} = 25 A) (I_{TM} = 25 A, I_{R} = 25 A, I_{J} = 125°C)		t _q	_ _	15 35	_ _	μs
DYNAMIC CHARACTERISTICS						
Critical Rate of Rise of Off-State Voltage (Gate Open, Rated V _{DRM} , Exponential Waveform)		dv/dt	_	50	_	V/µs

^{*}Indicates JEDEC Registered Data.

^{2.} Pulse Test: Pulse Width $\leq 300~\mu s,$ Duty Cycle $\leq 2\%.$

Voltage Current Characteristic of SCR

Symbol	Parameter
V _{DRM}	Peak Repetitive Off State Forward Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Off State Reverse Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Peak On State Voltage
lu	Holding Current



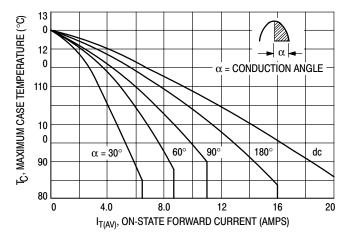
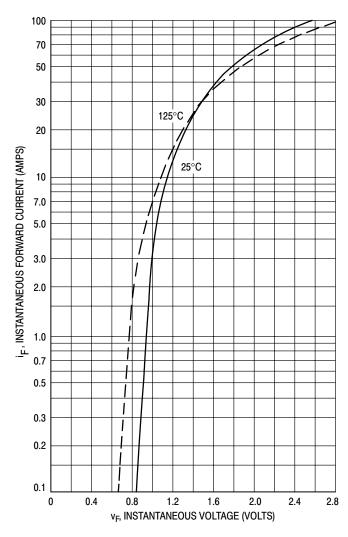


Figure 1. Average Current Derating

Figure 2. Maximum On-State Power Dissipation



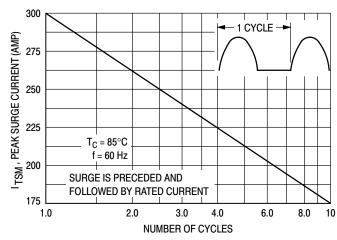


Figure 3. Typical On-State Characteristics

Figure 4. Maximum Non-Repetitive Surge Current

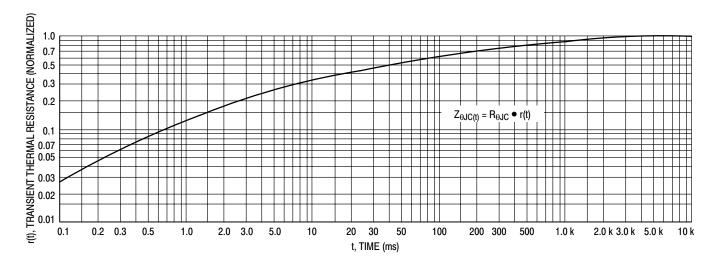


Figure 5. Thermal Response

TYPICAL TRIGGER CHARACTERISTICS

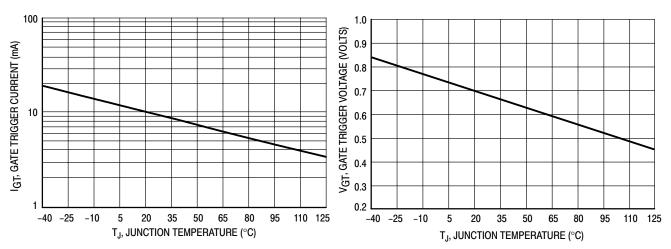


Figure 6. Typical Gate Trigger Current versus Junction Temperature

Figure 7. Typical Gate Trigger Voltage versus Junction Temperature

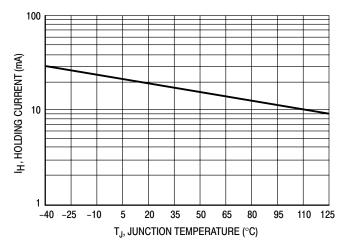
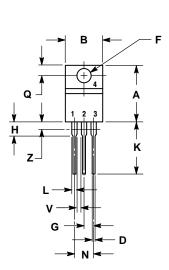
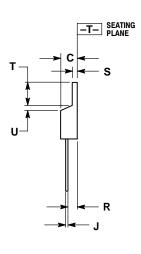


Figure 8. Typical Holding Current versus Junction Temperature

PACKAGE DIMENSIONS

TO-220AB CASE 221A-07 **ISSUE AA**





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

- STYLE 3:
 PIN 1. CATHODE
 2. ANODE
 3. GATE
 4. ANODE

Notes

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